Ordering number:EN1938A

NPN Triple Diffused Planar Silicon Transistor

2SC3686

Ultrahigh-Definition CRT Display Horizontal Deflection Output Applications

Applications

· Ultrahigh-definition color display horizontal deflection output.

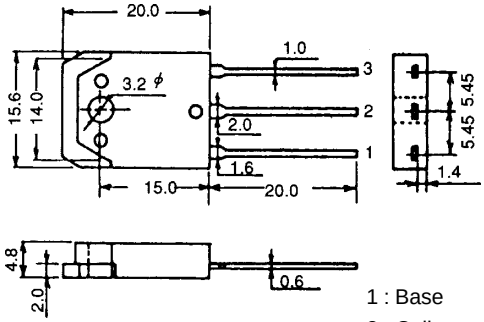
Features

· Fast speed (t_f typ=100ns).
· High breakdown voltage (V_{CBO}=1500V).
· High reliability (adoption of HVP process).
· Adoption of MBIT process.

Package Dimensions

unit:mm

2022A



1 : Base
2 : Collector
3 : Emitter
SANYO : TO-3PB

Specifications

Absolute Maximum Ratings at Ta = 25˚C

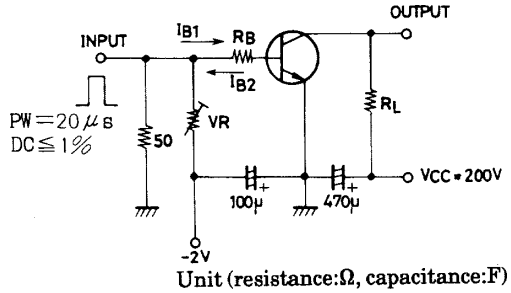
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		1500	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		7	A
Collector Current (Pulse)	I_{CP}		16	A
Collector Dissipation	P_C	Tc=25˚C	120	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CES}	V_{CE}=1500V, R_{BE}=0			1.0	mA
Collector-to-Emitter Sastain Voltage	$V_{CEO(sus)}$	I_C=100mA, I_B=0	800			V
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0			1.0	mA
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=5A, I_B=1.2A			5	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=5A, I_B=1.2A			1.5	V
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=1.0A	8			
Storage Time	t_{stg}	I_C=4A, I_{B1}=0.8A, I_{B2}=–1.6A			3.0	µs
Fall Time	t_f	I_C=4A, I_{B1}=0.8A, I_{B2}=–1.6A		0.1	0.2	µs

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Switching Time Test Circuit



Unit (resistance:Ω, capacitance:F)